

Table S1. Voltage gating parameters, V_0 and n , of VDAC-Cys pre-treated with 0.02mM Cu-Ph prior to channel reconstitution. Before (VDAC-Cys + Cu-Ph) and 20 minutes after (VDAC-Cys + Cu-Ph + DTT) the addition of 0.1mM DTT into the membrane-surrounding buffer solutions. Data are compared with VDAC WT. Voltage-gating parameters V_0 , the voltage at which half channels open, and n , the effective gating charge, were calculated from the open probability plots (Fig. S1) at positive and negative voltages. Data are means \pm STD and the numbers of experiments per condition are displayed in brackets.

	Positive potentials		Negative potentials	
	V_0 , mV	n	V_0 , mV	n
rmVDAC				
VDAC-Cys + Cu-Ph (2)	16.0 \pm 3.8	3.4 \pm 2.0	22.5 \pm 6.7	2.6 \pm 0.3
VDAC-Cys + Cu-Ph + DTT (3)	28 \pm 2.1	4.5 \pm 1.0	23.7 \pm 5.8	2.3 \pm 0.8
VDAC WT (2)	37.5 \pm 2.4	2.8 \pm 0.5	23.8 \pm 3.5	2.6 \pm 0.2